Dual N-ch 20V Fast Switching MOSFETs

★ Green Device Available
★ Super Low Gate Charge
★ Excellent Cdv/dt effect decline
★ Advanced high cell density Trench technology

Product Summary

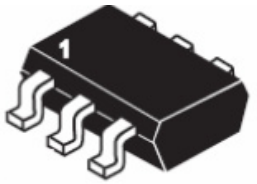
Green

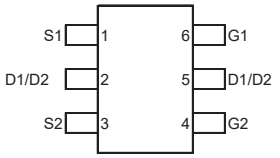
BVDSS	RDSON	ID
20V	12mΩ	7A

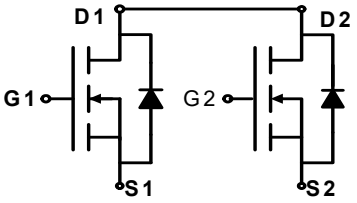
Description

The XR8810 is the high cell density trenched N-ch MOSFETs, which provides excellent RDSON and efficiency for most of the small power switching and load switch applications. The XR8810 meet the RoHS and Green Product requirement with full function reliability approved.

SOT23-6L Pin Configuration







Absolute Maximum Ratings (T_A=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	±10	V
Drain Current-Continuous	I_D	7	A
Drain Current-Pulsed (Note 1)	I_{DM}	25	A
Maximum Power Dissipation	P_D	1.25	W
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 150	℃

Thermal Characteristic

Thermal Resistance,Junction-to-Ambient (Note 2)	$R_{\theta JA}$	100	℃/W

Gate-Body Leakage Current	I_{GSS}	V_{GS}=±12V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250μA	0.5	0.7	1.2	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=4.5V, I_D=4.5A	-	12	15	mΩ
		V_{GS}=2.5V, I_D=3.5A	-	14	18	mΩ
Forward Transconductance	g_{FS}	V_{DS}=5V,I_D=4.5A	-	10	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=10V,V_{GS}=0V, F=1.0MHz	-	900	-	PF
Output Capacitance	C_{oss}		-	220	-	PF
Reverse Transfer Capacitance	C_{rss}		-	100	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=10V,I_D=1A V_{GS}=4.5V,R_{GEN}=6Ω	-	10	20	nS
Turn-on Rise Time	t_r		-	11	25	nS
Turn-Off Delay Time	$t_{d(off)}$		-	35	70	nS
Turn-Off Fall Time	t_f		-	30	60	nS
Total Gate Charge	Q_g	V_{DS}=10V,I_D=6A, V_{GS}=4.5V	-	12	15	nC
Gate-Source Charge	Q_{gs}		-	2.3	-	nC
Gate-Drain Charge	Q_{gd}		-	1	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=1.7A	-	0.75	1.2	V
Diode Forward Current (Note 2)	I_S		-	-	6.5	A

Typical Electrical and Thermal Characteristics

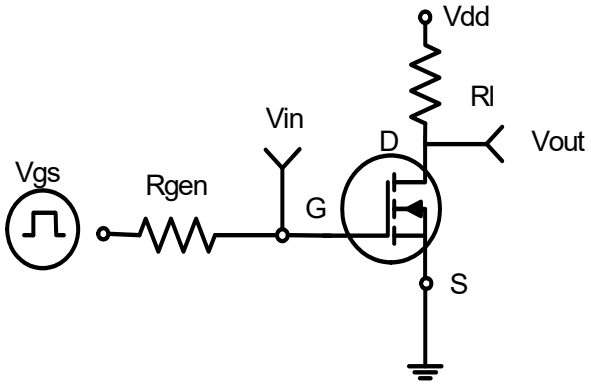


Figure 1:Switching Test Circuit

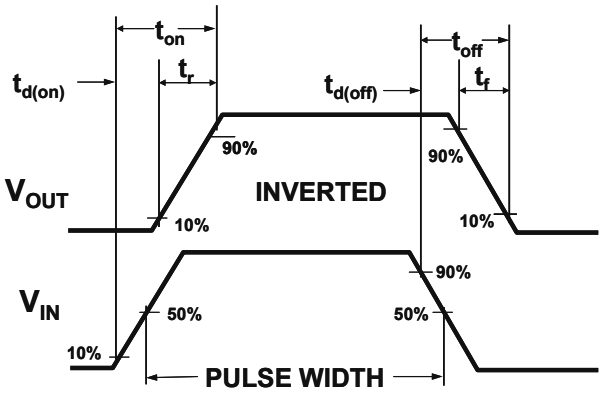


Figure 2:Switching Waveforms

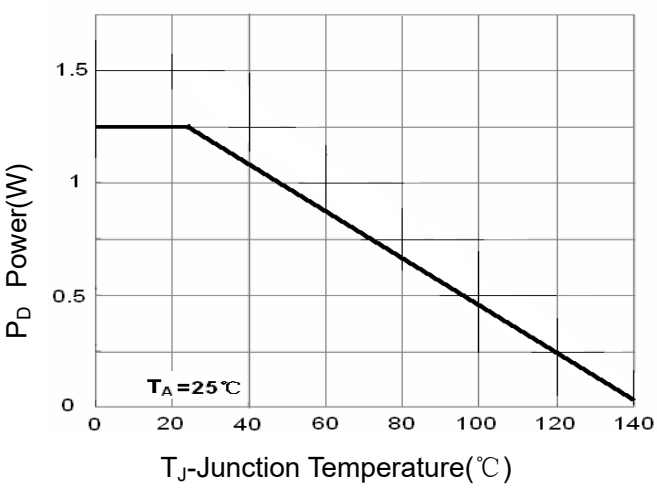


Figure 3 Power Dissipation

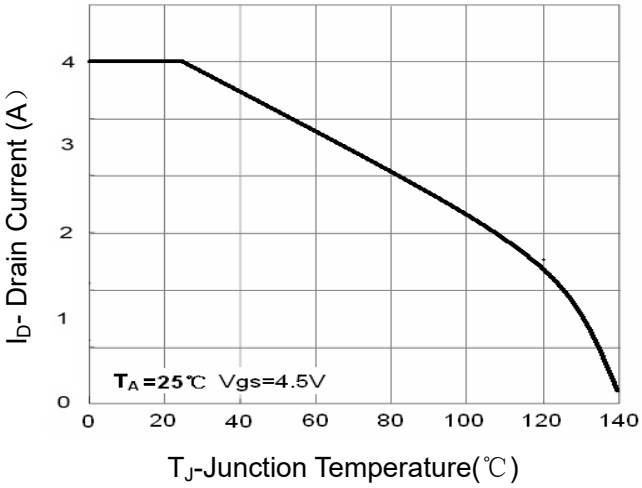


Figure 4 Drain Current

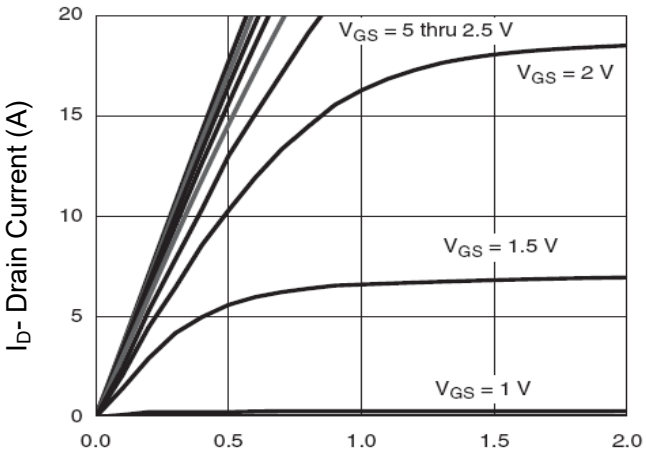


Figure 5 Output Characteristics

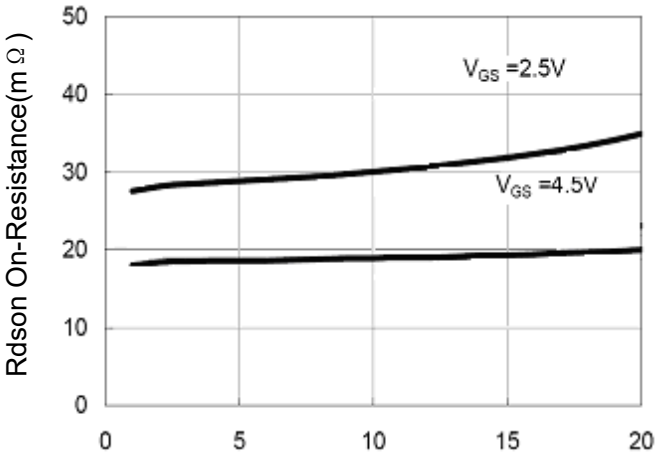


Figure 6 Drain-Source On-Resistance

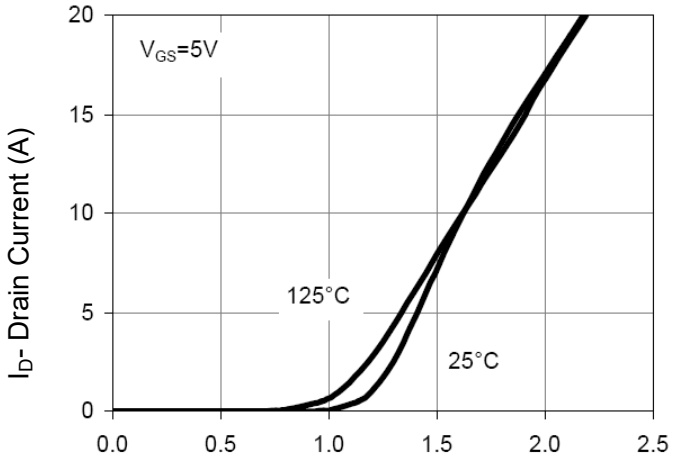


Figure 7 Transfer Characteristics

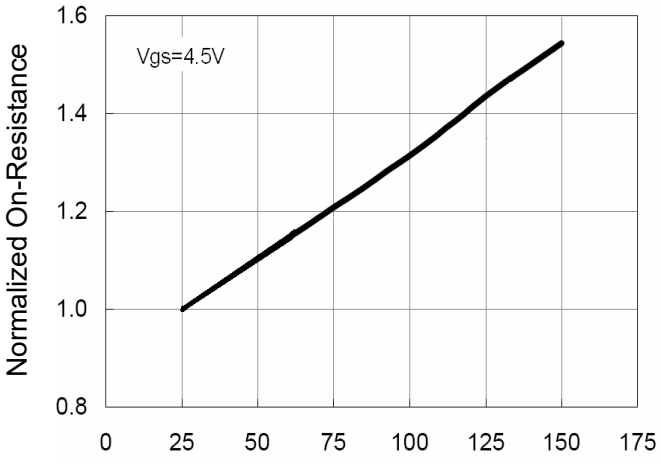


Figure 8 Drain-Source On-Resistance

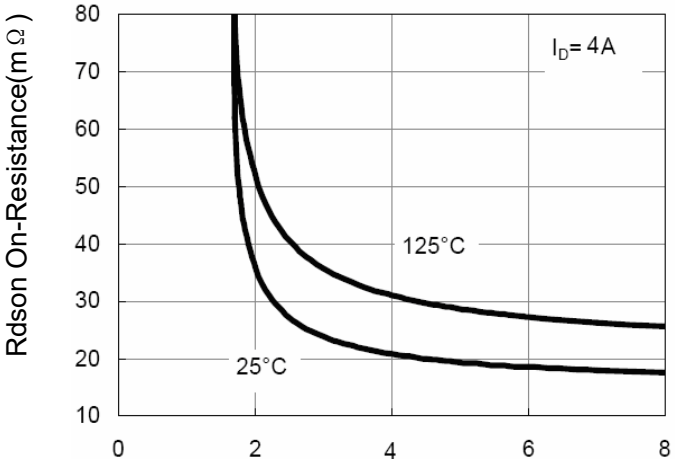


Figure 9 Rdson vs Vgs

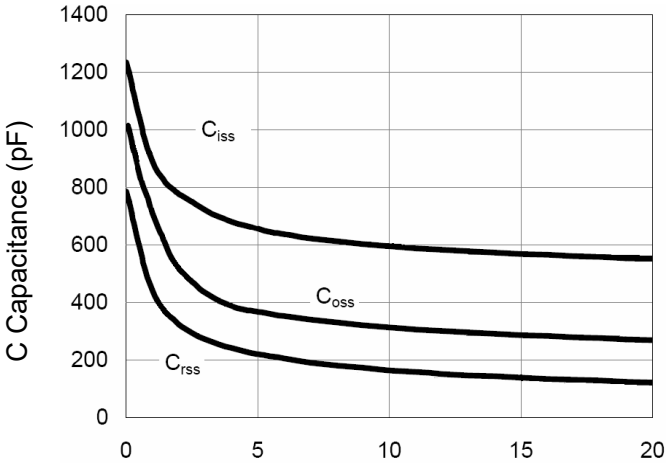


Figure 10 Capacitance vs Vds

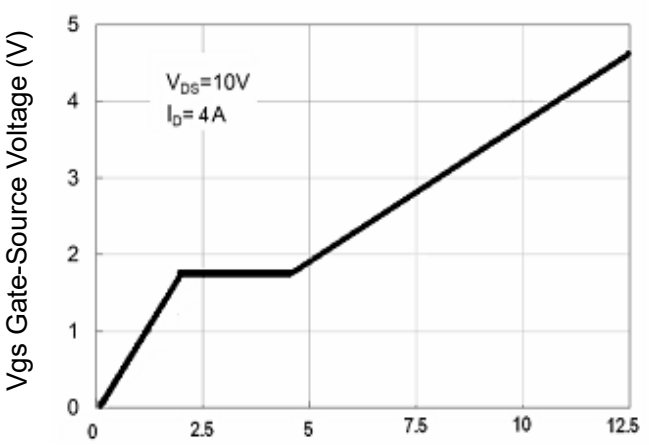


Figure 11 Gate Charge

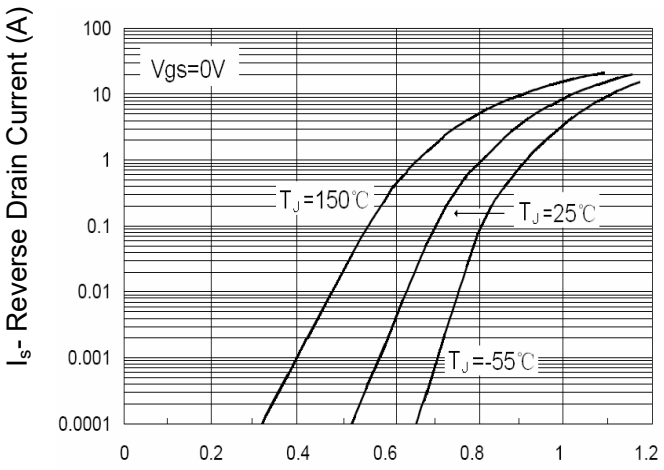


Figure 12 Source- Drain Diode Forward

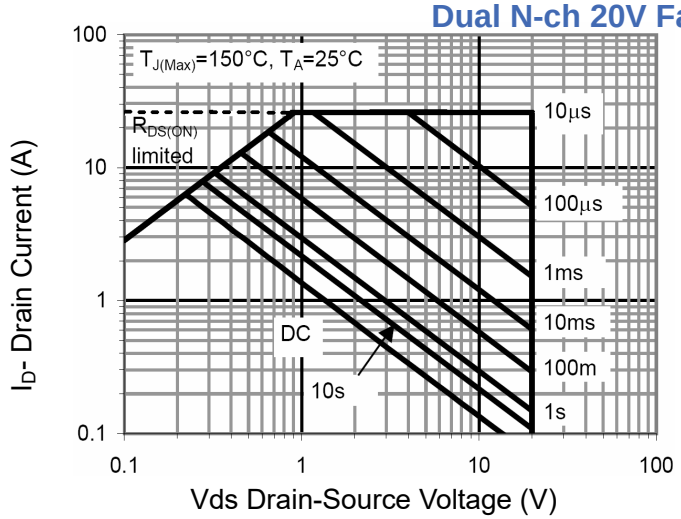


Figure 13 Safe Operation Area

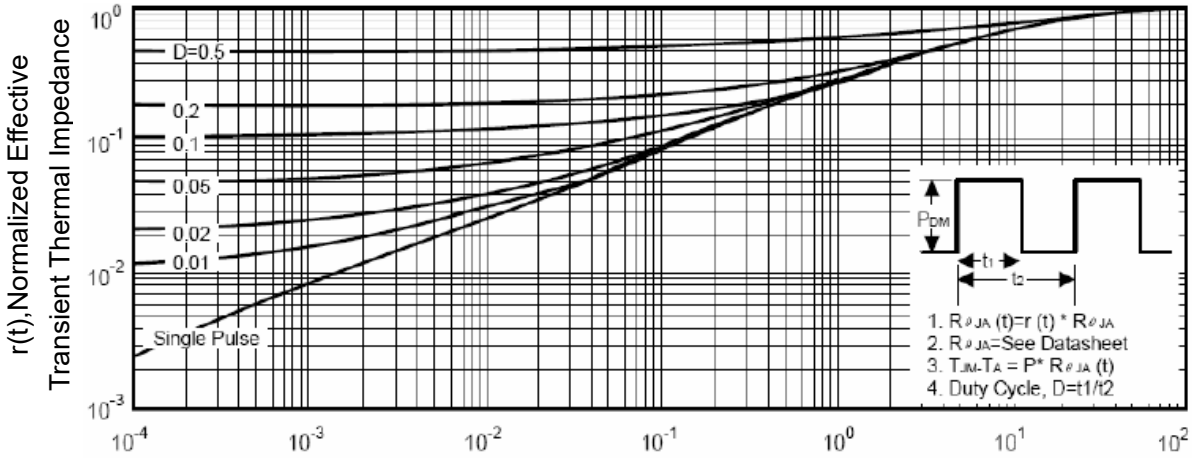
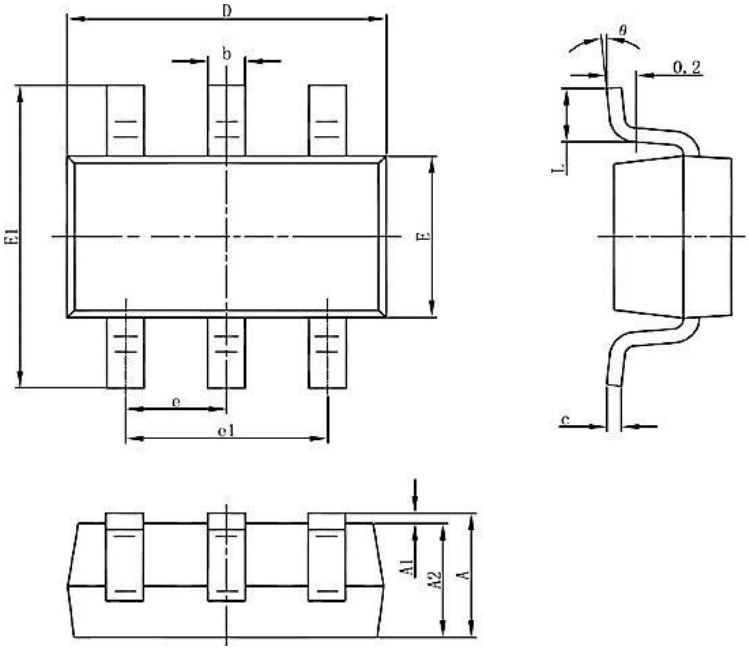


Figure 14 Normalized Maximum Transient Thermal Impedance

SOT23-6L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
C	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950（BSC）		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0	8	0	8